

SSC8040GS6

N-Channel Enhancement Mode MOSFET

Features \triangleright

V _{DS}	V _{GS}	R _{DS(ON)} Typ.	ID
40V	±20V	24mΩ@10V	9A
		29mΩ@4V5	34

> Description

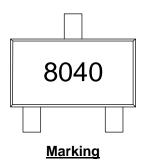
This device uses advanced trench technology to provide excellent RDSON and low gate charge. This device is suitable for use as a load switch or in PWM applications.

Applications \geq

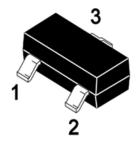
- Load Switch •
- Portable Devices •
- **DCDC** Conversion

> Ordering Information

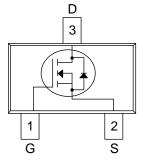
Device	Package	Shipping
SSC8040GS6	SOT-23	3000/Reel







SOT-23



Pin Configuration (Top View)





Symbol	Parameter	Ratings	Unit	
V _{DSS}	Drain-to-Source Voltage	to-Source Voltage 40		
V _{GSS}	Gate-to-Source Voltage ±20			
ID	Continuous Drain Current ^a 9		А	
Ідм	Pulsed Drain Current ^b	36	А	
PD	Power Dissipation ^c	1.25	W	
TJ	Operation junction temperature	-55~150	°C	
T _{STG}	Storage temperature range	-55~150	°C	

> Absolute Maximum Ratings ($T_A=25^{\circ}C$ unless otherwise noted)

> Thermal Resistance Ratings ($T_A=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Maximum	Unit
Reja	Junction-to-Ambient Thermal Resistance ^a	98	°C/W

Note:

- a. The value of R_{θJA} is measured with the device mounted on 1 in² FR-4 board with 2oz.copper, in a still air environment with T_A=25 °C.The value in any given application depends on the user is specific board design. The power dissipation is based on the t≤10s thermal resistance rating.
- b. Repetitive rating, pulse width limited by junction temperature.
- c. The power dissipation P_D is based on T_{J(MAX)}=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heat sinking is used.



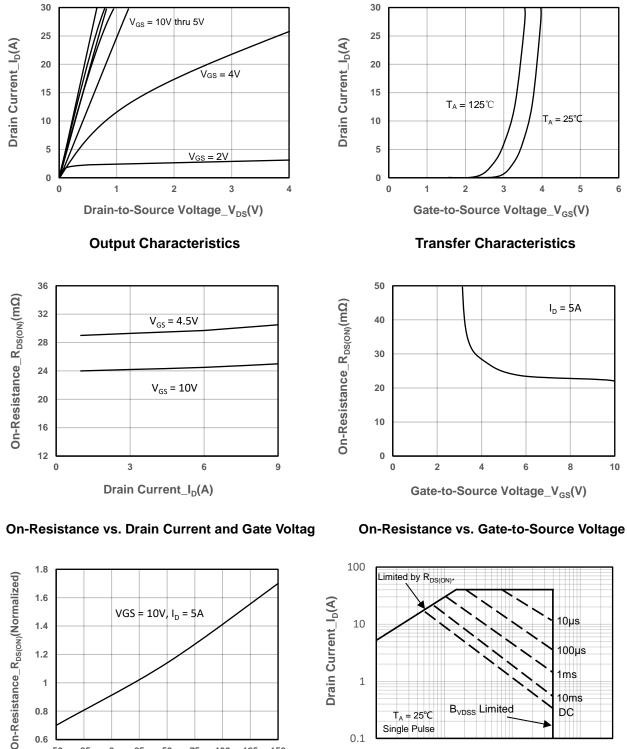


> Electrical Characteristics (T_A=25 $^{\circ}$ C unless otherwise noted)

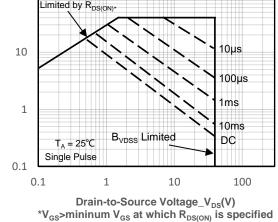
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Drain-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0V, I_D = 250 \mu A$	40			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250 uA$	1	1.5	2.5	V
	RDS(on)	$V_{GS} = 10V, I_D = 5.8A$		24	33	mΩ
Drain-Source On-Resistance		V _{GS} = 4.5V, I _D = 5A		29	38	
Zero Gate Voltage Drain Current	IDSS	$V_{DS} = 40V, V_{GS} = 0V$			1	μA
Gate-Source Leak Current	lgss	$V_{GS} = \pm 20V$, $V_{DS} = 0V$			±100	nA
Transconductance	G _{FS}	$V_{DS} = 5V, I_D = 1A$		20		s
Forward Voltage	V _{SD}	V _{GS} = 0V, I _S = 1A			1.3	V
Input Capacitance	Ciss			530		
Output Capacitance	Coss	$V_{DS} = 20V, V_{GS} = 0V,$		68		pF
Reverse Transfer Capacitance	C _{RSS}	f = 1MHz		58		
Turn-on Delay Time	T _{D(ON)}			11		
Rise Time	Tr	V _{GS} = 10V, I _D = 5A,		9		- ns
Turn-off Delay Time	T _{D(OFF)}	V_{DS} = 20V, R_G = 3 Ω		15		
Fall Time	T _f			10		
Total Gate Charge	Q_{G}			13.5		nC
Gate to Source Charge	Q _{GS}	$V_{GS} = 10V, V_{DS} = 20V,$		1.7		
Gate to Drain Charge	Q_{GD}	I _D = 5A		2.2		



Typical Performance Characteristics (T_A=25℃ unless otherwise noted) \triangleright



On-Resistance vs. Junction Temperature



Safe Operating Area vs. Junction-to-Ambient

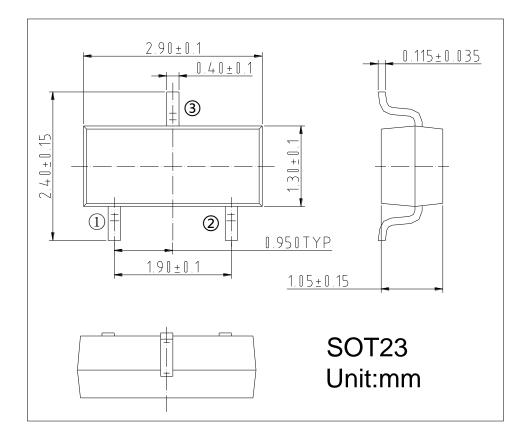
0.8

0.6

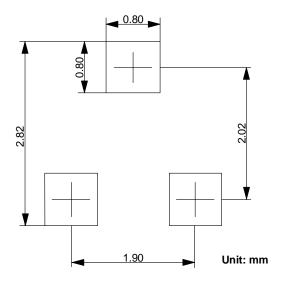




> Package Information



Recommended Pad outline





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